

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring direct interfacing to logic level ICs and low power gate drivers.

2. Features and benefits

- · Direct interfacing to logic level ICs
- · Direct interfacing to low power gate drive circuits
- · High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- · Sensitive gate in four quadrants
- Surface-mountable package
- Triggering in all four quadrants

3. Applications

- General purpose low power motor control
- Home appliances
- · Industrial process control
- Low power AC Fan controllers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$; Fig. 2; Fig. 3	-	-	1	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; $Fig. 4$; $Fig. 5$	-	-	8	А
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$	-	-	8.5	А
Tj	junction temperature		-	-	125	°C
Static charact	teristics					,
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 9}}{}$	-	-	10	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$	-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	10	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.3	1.6	V
Dynamic char	acteristics					,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 14	50	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T_j = 110 °C; $dI_{com}/$ dt = 0.44 A/ms; gate open circuit	2	-	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2——T1
2	T2	main terminal 2		G sym051
3	G	gate		symosi
4	T2	main terminal 2	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information

Table of Oracining interior						
Type number	Package	ckage				
	Name	Description	Version			
Z0109NN	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 105 \text{ °C}$; Fig. 1; Fig. 2; Fig. 3	-	1	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	8	Α
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	8.5	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.32	A²s
dl _⊤ /dt	rate of rise of on-state	I _G = 20 mA; T2+ G+	-	50	A/µs
	current	I _G = 20 mA; T2+ G-	-	50	A/µs
		I _G = 20 mA; T2- G-	-	50	A/µs
		I _G = 20 mA; T2- G+	-	20	A/µs
I _{GM}	peak gate current		-	1	Α
P_{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

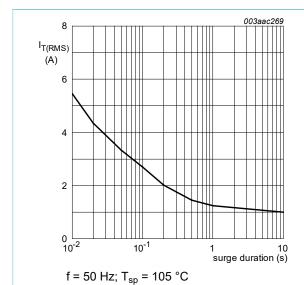


Fig. 1. RMS on-state current as a function of surge duration; maximum values

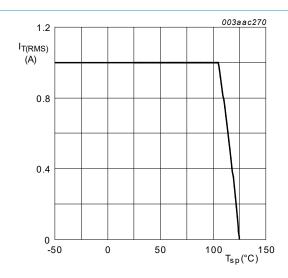


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

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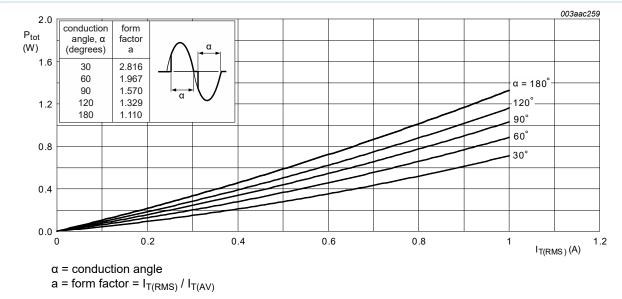


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

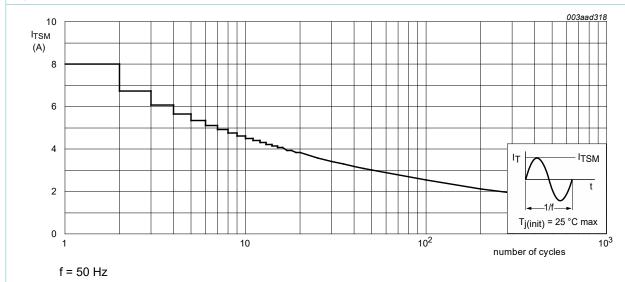
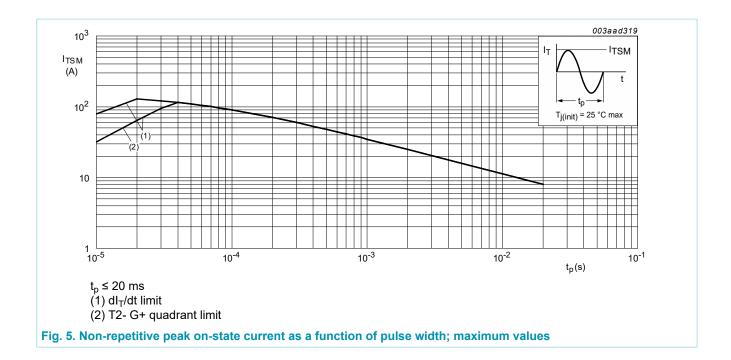


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full cycle; Fig. 6	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to	full cycle; printed circuit board mounted; minimum footprint; Fig. 7	-	156	-	K/W
	ambient free air	full cycle; printed circuit board mounted; pad area; Fig. 8	-	70	-	K/W

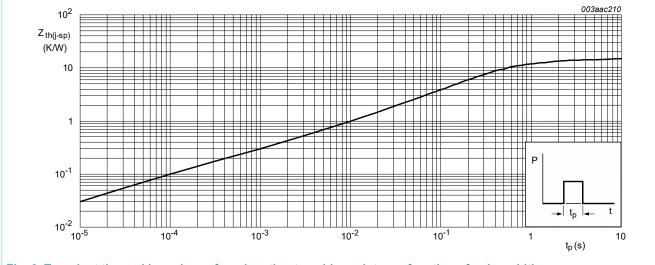
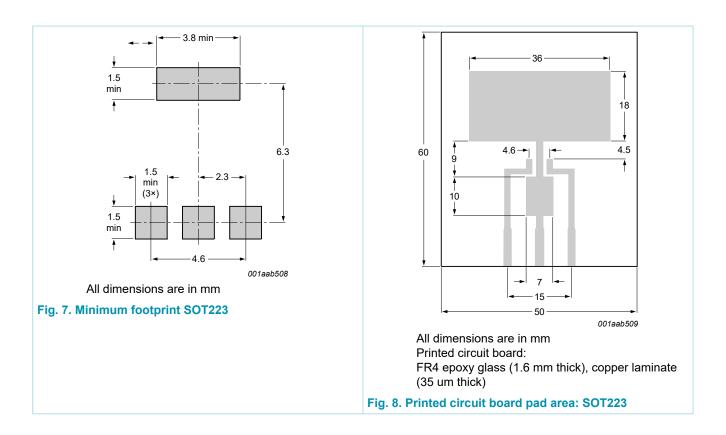


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		,			
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; Fig. 9	-	-	10	mA
L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	15	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 10</u>	-	-	25	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 10</u>	-	-	15	mA
		V _D = 12 V; I _G = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 10</u>	-	-	15	mA
Н	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	10	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 13	-	-	1	V
		$V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$ Fig. 13	0.2	-	-	V
D	off-state current	V _D = 800 V; T _j = 125 °C	-	-	0.5	mA
Dynamic ch	naracteristics		,			,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 14	50	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 110 ^{\circ}\text{C}; \text{dI}_{com}/$ dt = 0.44 A/ms; gate open circuit	2	-	-	V/µs

3

2

0

-50

I_{L(25°C)}

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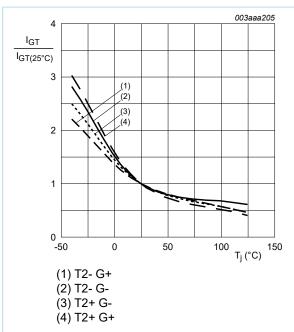


Fig. 10. Normalized latching current as a function of junction temperature

50

100

T_i (°C)

150

0



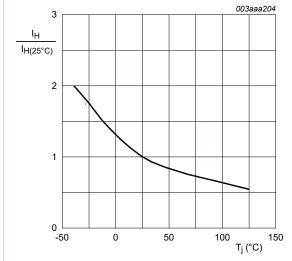
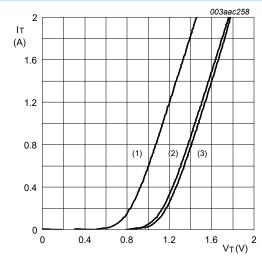


Fig. 11. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$ $R_s = 0.31 \Omega$

(1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

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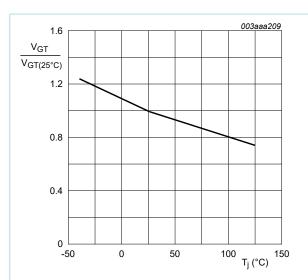


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

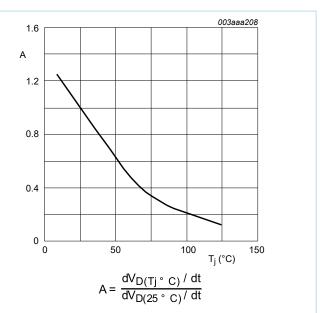


Fig. 14. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

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10. Package outline

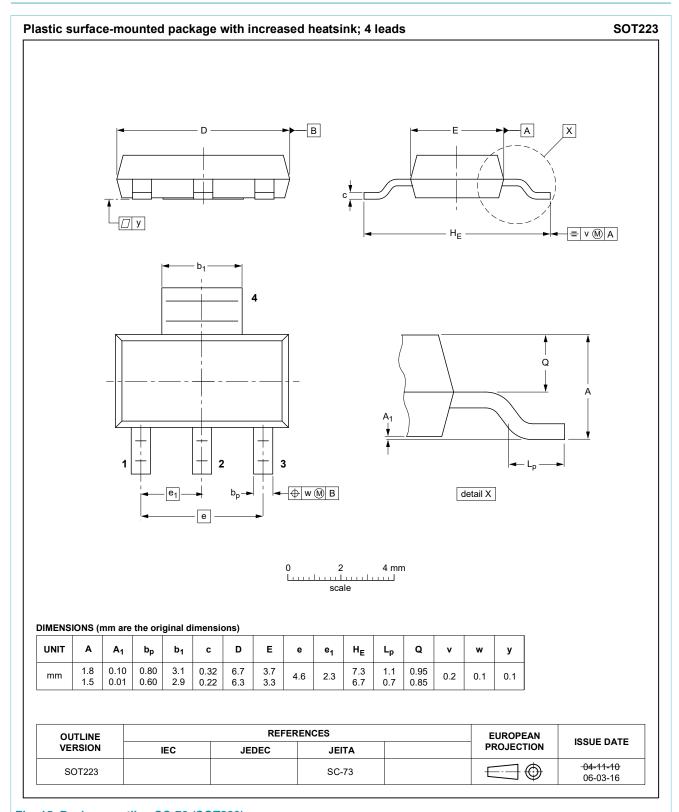


Fig. 15. Package outline SC-73 (SOT223)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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